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In the Claims

1. (Canceled)
2. (Currently Amended) The optical transistor of claim 4-18, wherein said light intensity modulator region is formed on a substrate and is separated by a first terminal disposed on one surface of said substrate and a second terminal disposed on other surface of said substrate.
3. (Currently Amended) The optical transistor of claim 4-18, wherein said light intensity modulator region is bi-stable.
4. (Currently Amended) The optical transistor of claim 4-18, wherein said light intensity modulator region is liquid crystal.
5. (Currently Amended) The optical transistor of claim 4-18, wherein said light intensity modulator region is optical crystal.
6. (Currently Amended) The optical transistor of claim 4-18, wherein said light intensity modulator region exhibits high gain.
7. (Currently Amended) The optical transistor of claim 4-18, wherein said light intensity modulator region exhibits negative gain.
8. (Canceled)
9. (Currently Amended) The optical transistor of claim 4-18, wherein said light intensity modulator region is configured for specified wavelength bands.
10. (Currently Amended) The optical transistor of claim 4-18, further comprising:  
a control light incident on at least one of said first photo conductor region or said second photo conductor region.
11. (Canceled)
12. (Canceled)
13. (Canceled)
14. (Currently Amended) The optical transistor of claim 4-18, wherein said photo conductor regions comprise input logic operators.
15. (Currently Amended) The optical transistor of claim 14 wherein said second terminal comprise output logic operators.
16. (Currently Amended) An array of a plurality of optical transistors of claim 4-18.

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17. (Currently Amended) An array of a plurality of optical transistors of claim 1-2 comprising:
- a first array of said optical transistors; and
  - a second array of said optical transistors with a plurality of first terminals disposed incident to a plurality of second terminals of light intensity modulator drain regions of said first array.
18. (New) An optical transistor comprising:
- a light intensity modulator region; and
  - a first photo conductor region and a second photo conductor region operably coupled to said light intensity modulator region for controlling said light intensity modulator region.
19. (New) The optical transistor of claim 18, further comprising:
- a first control light incident on said first photo conductor region, a second control light incident on said second photo conductor region, and an input light incident on said light intensity modulator region.
20. (New) The optical transistor of claim 19, further comprising:
- an output light emanating from said light intensity modulator region.
21. (New) An array of a plurality of optical transistors comprising:
- a first array of optical transistors; and
  - a second array of optical transistors,
- wherein said optical transistors include
- a light intensity modulator region; and
  - a photo conductor region operably coupled to said light intensity modulator region for controlling said light intensity modulator region.

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